



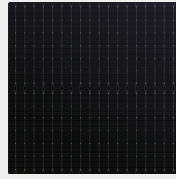


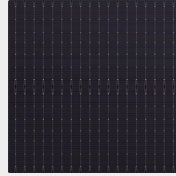
# TM1218 N-Type TOPCon

## KEY FEATURES

-  High Photoelectric Conversion Efficiency
-  Higher Power Generation
-  Excellent Resistance to Hidden Cracks
-  Higher Efficiency in Power Generation



Front



Back

**Size :** 210mm\*210mm±0.25mm

**Thickness :** 130±13µm

**Solderability :** ≥0.5N/mm

The results may vary depending to DS,welding methods and conditions.

## Technical Data And Design

**Power:** -0.32%/K

**Voltage:** -0.26 %/K

**Current:** +0.046%/K

**Front :** 18 \* 0.04 ± 0.03mm main gate line (silver), 120 ± 12 secondary gate lines blue (dark blue), anti-reflective film (silicon nitride)

**Back :** 18 \* 0.04 ± 0.03mm Back electrode width (silver) 138± 14 mm sub -grid lines

Rsh≥35Ω, Irev2≤1.0A

## Front Electrical Performance Parameters

Eff(%)	FF(%)	Pmpp (W)	I <sub>mp</sub> (A)	U <sub>mp</sub> (V)	I <sub>sc</sub> (A)	U <sub>oc</sub> (V)
25.6	83.39	11.289	17.805	0.634	18.494	0.732
25.5	83.22	11.244	17.764	0.633	18.485	0.731
25.4	83.05	11.200	17.722	0.632	18.474	0.730
25.3	82.87	11.156	17.680	0.631	18.467	0.729
25.2	82.71	11.112	17.638	0.630	18.454	0.728

## Iv Curve

